Unit: mm

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSV)

# 2SK2662

# DC-DC Converter, Relay Drive and Motor Drive Applications

• Low drain-source ON resistance :  $RDS(ON) = 1.35 \Omega \text{ (typ.)}$ 

• High forward transfer admittance  $: |Y_{fs}| = 4.0 \text{ S (typ.)}$ 

• Low leakage current :  $IDSS = 100 \mu A (max) (VDS = 500 V)$ 

• Enhancement-mode :  $V_{th} = 2.0 \sim 4.0 \text{ V (V}_{DS} = 10 \text{ V, I}_{D} = 1 \text{ mA})$ 

### Maximum Ratings (Ta = 25°C)

Characteri	stics	Symbol	Rating	Unit	
Drain-source voltage		$V_{DSS}$	500	V	
Drain-gate voltage (Re	$GS = 20 \text{ k}\Omega$	$V_{DGR}$	500	V	
Gate-source voltage		V <sub>GSS</sub>	±30	V	
Drain current	DC (Note 1)	I <sub>D</sub>	5	Α	
	Pulse (Note 1)	I <sub>DP</sub>	20	Α	
Drain power dissipatio	n (Tc = 25°C)	P <sub>D</sub>	35	W	
Single pulse avalanche	e energy (Note 2)	E <sub>AS</sub>	180	mJ	
Avalanche current		I <sub>AR</sub>	5	Α	
Repetitive avalanche	energy (Note 3)	E <sub>AR</sub>	3.5	mJ	
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature ra	ange	T <sub>stg</sub>	-55~150	°C	

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Weight: 1.9 g (typ.)

#### **Thermal Characteristics**

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R <sub>th (ch-c)</sub>	3.57	°C/W
Thermal resistance, channel to ambient	R <sub>th (ch-a)</sub>	62.5	°C/W

Note 1: Please use devices on condition that the channel temperature is below 150°C.

Note 2:  $V_{DD} = 90 \text{ V}$ ,  $T_{ch} = 25^{\circ}\text{C}$  (initial), L = 12.2 mH,  $R_G = 25 \Omega$ ,  $I_{AR} = 5 \text{ A}$ 

Note 3: Repetitive rating: Pulse width limited by maximum channel temperature

This transistor is an electrostatic sensitive device.

Please handle with caution.



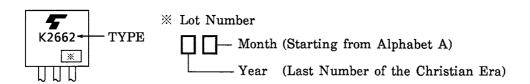
## **Electrical Characteristics (Ta = 25°C)**

Charac	eteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	rrent	I <sub>GSS</sub>	V <sub>GS</sub> = ±25 V, V <sub>DS</sub> = 0 V	_	_	±10	μΑ
Gate-source bre	eakdown voltage	V <sub>(BR)</sub> GSS	$I_G = \pm 10 \ \mu A, \ V_{DS} = 0 \ V$	±30	_	_	V
Drain cut-off cu	rrent	I <sub>DSS</sub>	V <sub>DS</sub> = 500 V, V <sub>GS</sub> = 0 V	_	_	100	μΑ
Drain-source br	eakdown voltage	V (BR) DSS	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	500	_	_	V
Gate threshold v	oltage	V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA	2.0	_	4.0	V
Drain-source O	N resistance	R <sub>DS</sub> (ON)	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 2.5 A	_	1.35	1.50	Ω
Forward transfer	admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 2.5 A	2.5	4.0	_	S
Input capacitano	e	C <sub>iss</sub>			780	_	pF
Reverse transfer capacitance		C <sub>rss</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	60	_	
Output capacitance		Coss		_	200	_	
Switching time	Rise time	t <sub>r</sub>	$V_{GS} = \frac{10V}{0V} = \frac{I_{D} = 2.5A}{V_{out}} = \frac{V_{out}}{V_{DD}} = \frac{10V}{225V}$ $V_{DD} = \frac{10V}{225V} = \frac{10V}{V_{DD}} = \frac{10V}{225V}$ $V_{DD} = \frac{10V}{225V} = \frac{10V}{V_{DD}} = \frac{10V}{225V}$	_	12	_	- ns
	Turn-on time	t <sub>on</sub>			25	_	
	Fall time	t <sub>f</sub>		l	15		
	Turn-off time	t <sub>off</sub>		-	60	_	
Total gate charge (gate-source plus gate-drain)		Qg			17		
Gate-source charge		Q <sub>gs</sub>	$V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 5 \text{ A}$		11	_	nC -
Gate-drain ("miller") Charge		$Q_{gd}$			6	_	

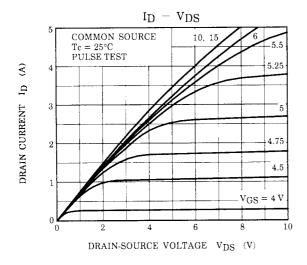
## **Source-Drain Ratings and Characteristics (Ta = 25°C)**

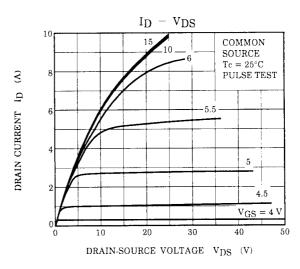
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I <sub>DR</sub>	_	_	_	5	Α
Pulse drain reverse current (Note 1)	I <sub>DRP</sub>	_	_	_	20	Α
Forward voltage (diode)	V <sub>DSF</sub>	I <sub>DR</sub> = 5 A, V <sub>GS</sub> = 0 V	_	_	-1.7	V
Reverse recovery time	t <sub>rr</sub>	I <sub>DR</sub> = 5 A, V <sub>GS</sub> = 0 V	_	1400	_	ns
Reverse recovery charge	Q <sub>rr</sub>	dl <sub>DR</sub> / dt = 100 A / μs	_	9	_	μC

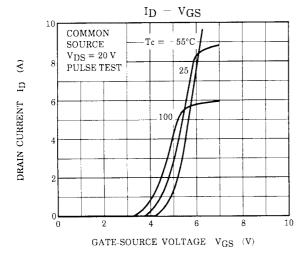
# Marking

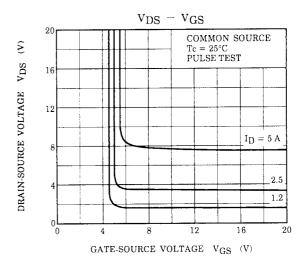


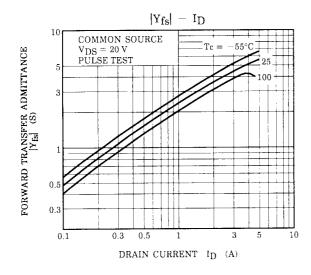
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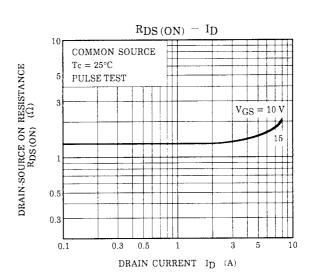




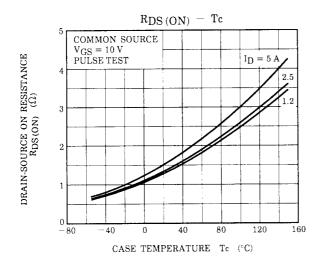


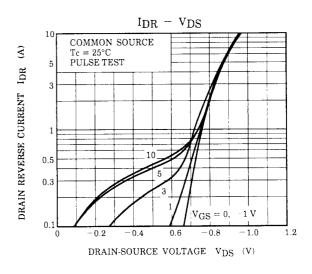


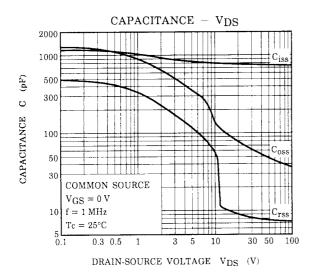


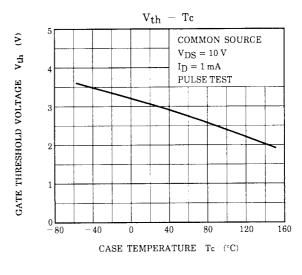


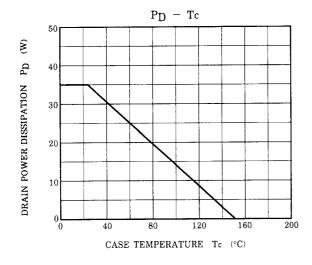
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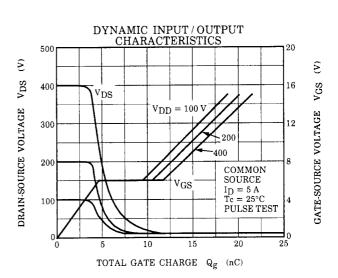




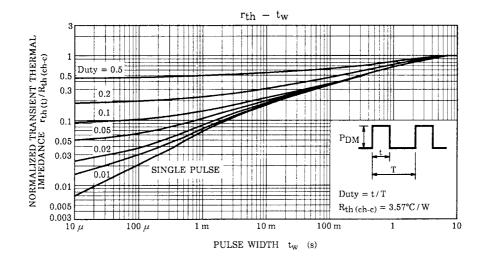


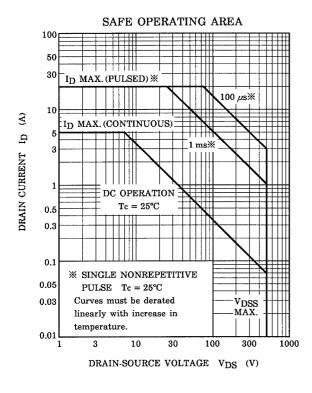


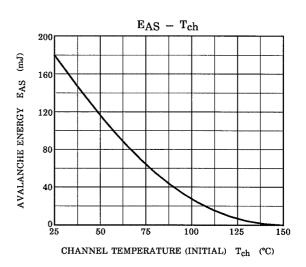


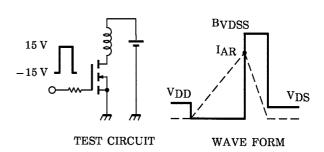


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$$\begin{aligned} &RG = 25~\Omega \\ &V_{DD} = 90~V,~L = 12.2~mH \end{aligned} \quad E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left( \frac{BV_{DSS}}{BV_{DSS} - V_{DD}} \right)$$

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